

## Low-voltage stabistor

BAS17

## FEATURES

- Low-voltage stabilization
- Forward voltage range: 580 to 960 mV
- Total power dissipation: max. 250 mW.

## APPLICATIONS

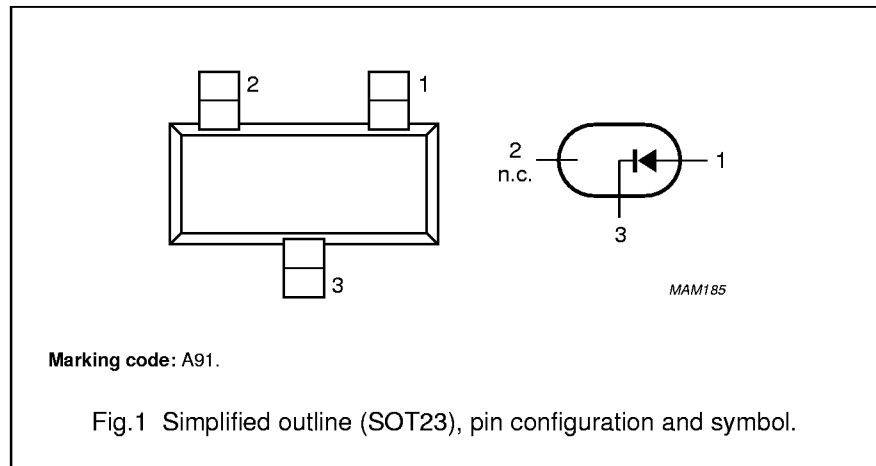
- Low-voltage stabilization e.g.
  - Bias stabilizer in class-B output stages
  - Clipping
  - Clamping
  - Meter protection.

## DESCRIPTION

Low-voltage stabilization diode in a small SOT23 plastic package.

## PINNING

PIN	DESCRIPTION
1	anode
2	not connected
3	cathode



## LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_R$	continuous reverse voltage		–	5	V
$I_F$	continuous forward current		–	200	mA
$P_{tot}$	total power dissipation	$T_{amb} = 25\text{ °C}$	–	250	mW
$T_{stg}$	storage temperature		–65	+150	°C
$T_j$	junction temperature		–	150	°C

## ELECTRICAL CHARACTERISTICS

$T_j = 25\text{ °C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_F$	forward voltage	see Fig.2				
		$I_F = 0.1\text{ mA}$	580	–	660	mV
		$I_F = 1\text{ mA}$	665	–	745	mV
		$I_F = 5\text{ mA}$	725	–	805	mV
		$I_F = 10\text{ mA}$	750	–	830	mV
$I_F = 100\text{ mA}$	870	–	960	mV		
$I_R$	reverse current	$V_R = 4\text{ V}$	–	–	5	$\mu\text{A}$
$r_{dif}$	differential resistance	$I_F = 0.5\text{ mA}$	–	120	–	$\Omega$
		$I_F = 2\text{ mA}$	–	80	–	$\Omega$
$S_F$	temperature coefficient	$I_F = 1\text{ mA}$	–	–1.8	–	mV/K
$C_d$	diode capacitance	$V_R = 0\text{ V}; f = 1\text{ MHz}$	–	–	140	pF

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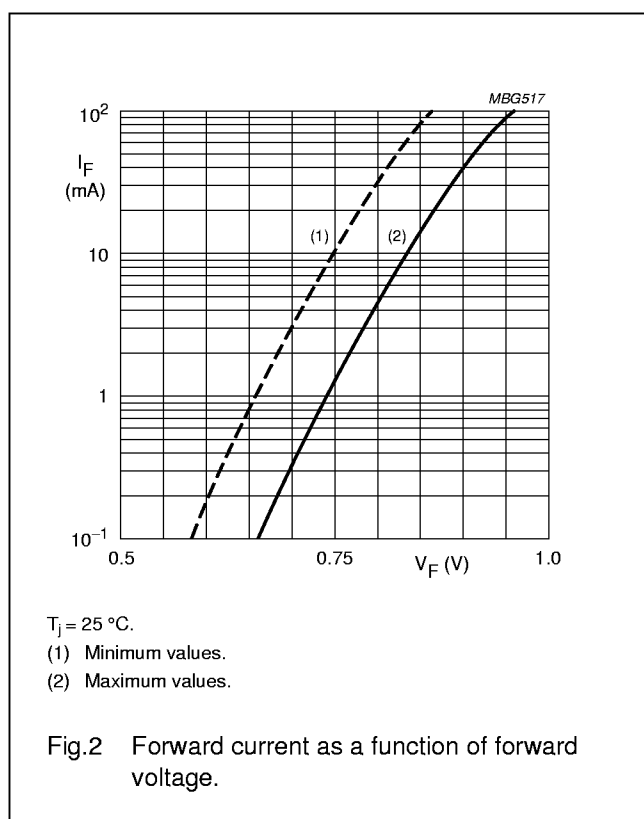
**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-tp}$	thermal resistance from junction to tie-point		330	K/W
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	500	K/W

**Note**

1. Device mounted on a FR4 printed-circuit board.

**GRAPHICAL DATA**



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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23

